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### February 2008

# FAIRCHILD

# FGL40N120AND 1200V NPT IGBT

# Features

- High speed switching
- Low saturation voltage :  $V_{CE(sat)} = 2.6 \text{ V} @ I_C = 40 \text{ A}$
- High input impedance
- CO-PAK, IGBT with FRD :  $t_{rr}$  = 75ns (typ.)

# Applications

Induction Heating, UPS, AC & DC motor controls and general purpose inverters.

## Description

Employing NPT technology, Fairchild's AND series of IGBTs provides low conduction and switching losses. The AND series offers an solution for application such as induction heating (IH), motor control, general purpose inverters and uninterruptible power supplies (UPS).



# Absolute Maximum Ratings

Symbol	Parameter		FGL40N120AND	Units	
V <sub>CES</sub>	Collector-Emitter Voltage		1200	V	
V <sub>GES</sub>	Gate-Emitter Voltage		±25	V	
1	Collector Current	@T <sub>C</sub> = 25°C	64	А	
I <sub>C</sub>	Collector Current	@T <sub>C</sub> = 100°C	40	А	
I <sub>CM(1)</sub>	Pulsed Collector Current		160	А	
I <sub>F</sub>	Diode Continuous Forward Current	@T <sub>C</sub> = 100°C	40	А	
I <sub>FM</sub>	Diode Maximum Forward Current		240	А	
D	Maximum Power Dissipation	@T <sub>C</sub> = 25°C	500	W	
P <sub>D</sub>	Maximum Power Dissipation	@T <sub>C</sub> = 100°C	200	W	
SCWT	Short Circuit Withstand Time, $V_{CE} = 600V$ , $V_{GE} = 15V$ , $T_C = 125^{\circ}C$		10	μs	
Т <sub>Ј</sub>	Operating Junction Temperature		-55 to +150	°C	
T <sub>STG</sub>	Storage Temperature Range		-55 to +150	°C	
Τ <sub>L</sub>	Maximum Lead Temp. for Soldering Purposes, 1/8" from Case for 5 seconds		300	°C	

Notes:

(1) Pulse width limited by max. junction temperature

## **Thermal Characteristics**

Symbol	Parameter	Тур.	Max.	Units
$R_{\theta JC}$ (IGBT)	Thermal Resistance, Junction-to-Case		0.25	°C/W
$R_{\theta JC}(DIODE)$	Thermal Resistance, Junction-to-Case		0.7	°C/W
$R_{ ext{ heta}JA}$	Thermal Resistance, Junction-to-Ambient		25	°C/W

Device Marking Device Pac		Package			e Width	Quantity		
		TO-264					25	
Electrica	al Chai	racteristics of th	ne IGBT T <sub>c</sub>	= 25°C unless otherwise not	ed			
Symbol		Parameter	C	onditions	Min.	Тур.	Max.	Units
Off Characte	eristics							
BV <sub>CES</sub>	Collector-Emitter Breakdown Voltage		age V <sub>GE</sub> = 0\	$V_{GE} = 0V, I_C = 1mA$				V
BV <sub>CES</sub> / ΔT <sub>J</sub>	Temperature Coefficient of Breakdown Voltage		down	$V_{GE} = 0V, I_C = 1mA$		0.6		V/°C
I <sub>CES</sub>	Collector	r Cut-Off Current	$V_{CE} = V_{CE}$	$V_{CE} = V_{CES}, V_{GE} = 0V$			1	mA
I <sub>GES</sub>	G-E Lea	kage Current		$V_{GE} = V_{GES}, V_{CE} = 0V$			±250	nA
On Characte	eristics							·
On Characteristics   V <sub>GE(th)</sub> G-E Threshold Voltage			I <sub>C</sub> = 250	I <sub>C</sub> = 250μA, V <sub>CE</sub> = V <sub>GE</sub>		5.5	7.5	V
02()			-	$I_{\rm C} = 40$ A, $V_{\rm GE} = 15$ V		2.6	3.2	V
V <sub>CE(sat)</sub> Collector to Emitter Saturation Voltage		I <sub>C</sub> = 40A	$I_{C} = 40A, V_{GE} = 15V,$ $T_{C} = 125^{\circ}C$		2.9		V	
		$I_{\rm C} = 64 {\rm A}$	$I_{C} = 64A, V_{GE} = 15V$		3.15		V	
Dynamic Ch	naracteris	tics						
C <sub>ies</sub>	Input Capacitance		۱ <i>۲</i> ۵۵			3200		pF
C <sub>oes</sub>	Output C	Capacitance		V <sub>CE</sub> = 30V, V <sub>GE</sub> = 0V f = 1MHz		370		pF
C <sub>res</sub>	Reverse Transfer Capacitance					125		pF
Switching C	haracteri	istics						
t <sub>d(on)</sub>	r	Delay Time				15		ns
t <sub>r</sub>	Rise Tim	e		$V_{CC} = 600V$ , $I_C = 40A$ , $R_G = 5\Omega$ , $V_{GE} = 15V$ , Inductive Load, $T_C = 25^{\circ}C$		20		ns
t <sub>d(off)</sub>	Turn-Off	Delay Time	$V_{cc} = 60$			110		ns
t <sub>f</sub>	Fall Time	9	$R_{G} = 5\Omega$			40	80	ns
Eon	Turn-On	Switching Loss	Inductive			2.3	3.45	mJ
E <sub>off</sub>	Turn-Off	Switching Loss				1.1	1.65	mJ
E <sub>ts</sub>	Total Sw	itching Loss				3.4	5.1	mJ
t <sub>d(on)</sub>	Turn-On	Delay Time		$V_{CC} = 600V, I_C = 40A, R_G = 5\Omega, V_{GE} = 15V,$		20		ns
t <sub>r</sub>	Rise Tim	e				25		ns
t <sub>d(off)</sub>	Turn-Off	Delay Time	V <sub>CC</sub> = 60			120		ns
t <sub>f</sub>	Fall Time	9	$R_{G} = 5\Omega$			45		ns
E <sub>on</sub>	Turn-On	Switching Loss	Inductive	Load, T <sub>C</sub> = 125°C		2.5		mJ
E <sub>off</sub>	Turn-Off	Switching Loss		]		1.8		mJ
E <sub>ts</sub>	Total Sw	itching Loss				4.3		mJ
Qg	Total Ga	te charge	\/			220	330	nC
Q <sub>ge</sub>	Gate-Em	nitter Charge		V <sub>CE</sub> = 600V, I <sub>C</sub> = 40A, V <sub>GE</sub> = 15V		25	38	nC
Q <sub>gc</sub>	Gate-Co	llector Charge	- GE - R			130	195	nC

Symbol	Parameter	Test Conditions		Min.	Тур.	Max.	Units
V <sub>FM</sub>	Diode Forward Voltage	I <sub>F</sub> = 40A	$T_{\rm C} = 25^{\circ}{\rm C}$		3.2	4.0	v
			$T_{\rm C} = 125^{\circ}{\rm C}$		2.7		
t <sub>rr</sub>	Diode Reverse Recovery Time	I <sub>F</sub> = 40A, di/dt = 200A/μs	$T_{\rm C} = 25^{\circ}{\rm C}$		75	112	- nS
			$T_{C} = 125^{\circ}C$		130		
Irr	Diode Peak Reverse Recovery Current		$T_{C} = 25^{\circ}C$		8	12	A
			$T_{\rm C} = 125^{\circ}{\rm C}$		13		
Q <sub>rr</sub>	Diode Reverse Recovery Charge		$T_{\rm C} = 25^{\circ}{\rm C}$		300	450	nC
			T <sub>C</sub> = 125°C		845		

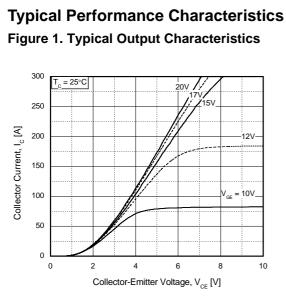


Figure 3. Saturation Voltage vs. Case Temperature at Variant Current Level

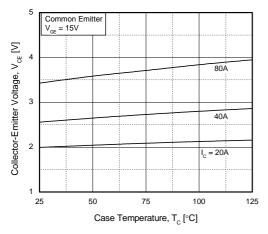


Figure 5. Saturation Voltage vs.  $V_{GE}$ 

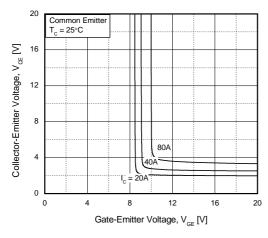


Figure 2. Typical Saturation Voltage Characteristics

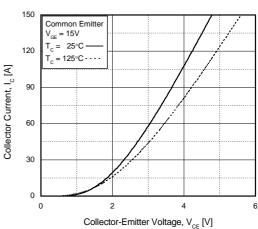


Figure 4. Load Current vs. Frequency

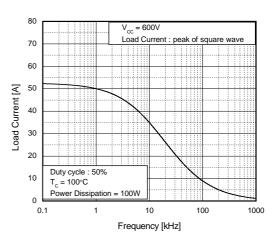
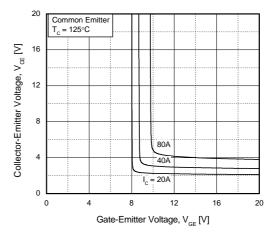
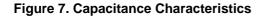


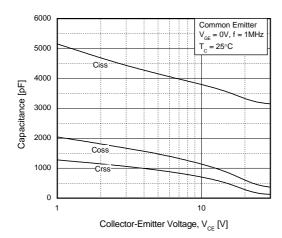
Figure 6. Saturation Voltage vs.  $V_{GE}$ 



FGL40N120AND 1200V NPT IGBT

# Typical Performance Characteristics (Continued)







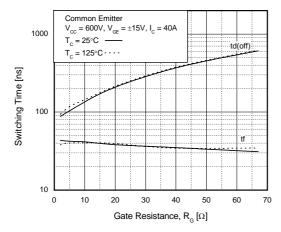


Figure 11. Turn-On Characteristics vs. Collector Current

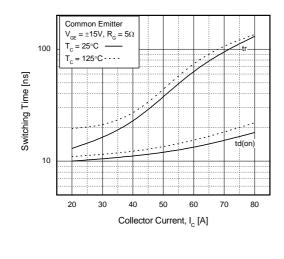


Figure 8. Turn-On Characteristics vs. Gate Resistance

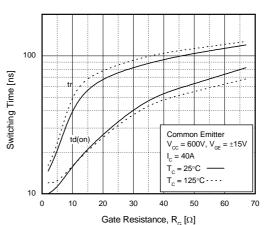


Figure 10. Switching Loss vs. Gate Resistance

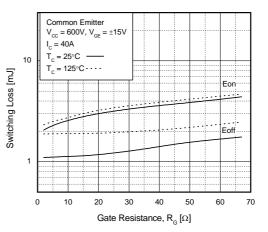
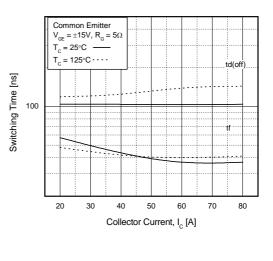
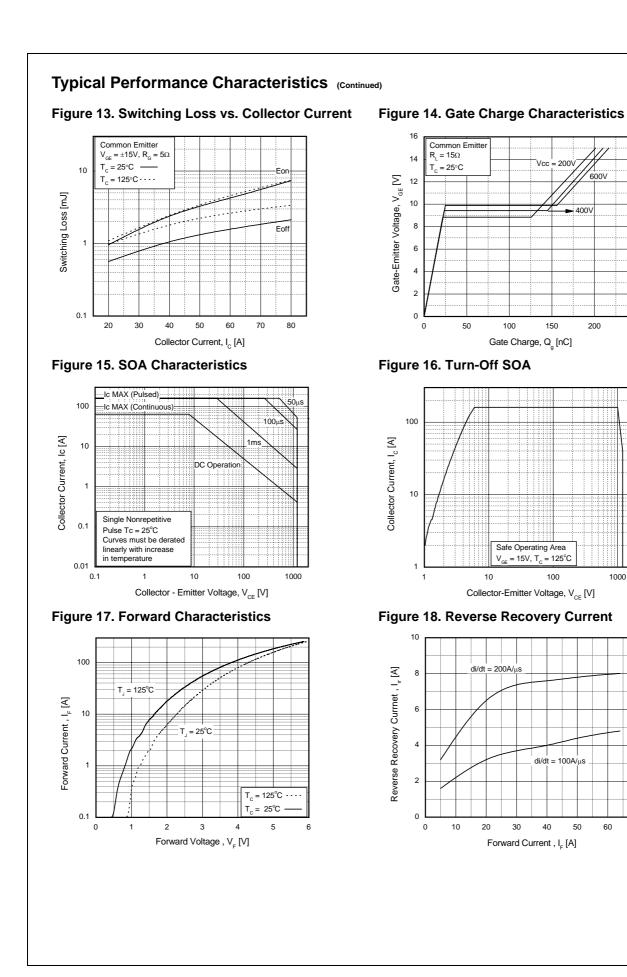


Figure 12. Turn-Off Characteristics vs. Collector Current

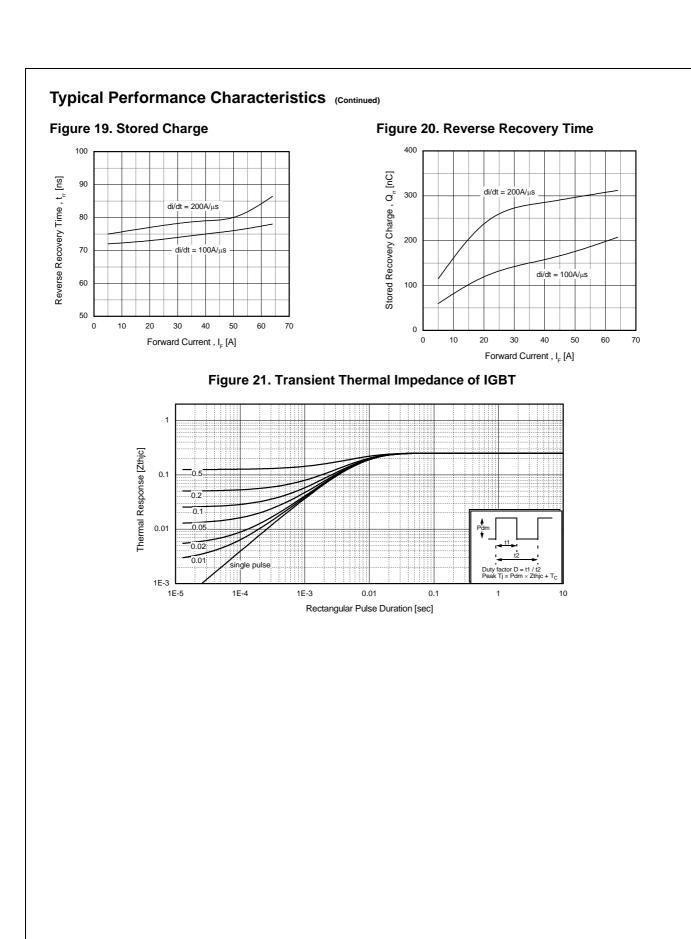


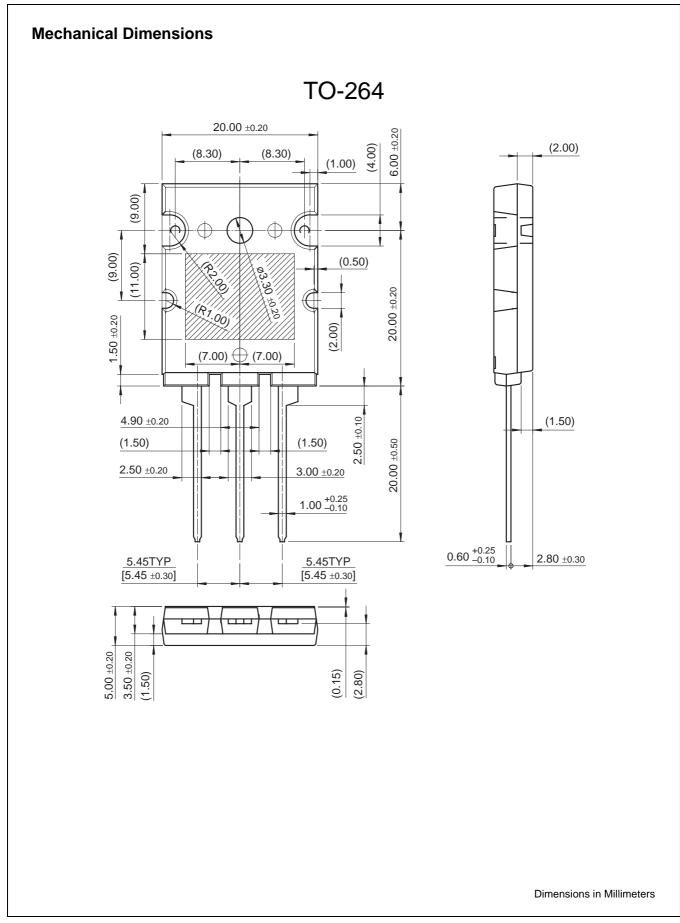
600V

400\



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